WHAT IS CLAIMED IS:

1. A bonding wire for semiconductor devices, comprising:
at least one selected from a group consisting of zinc (Zn), tin (Sn), and nickel (Ni) at 5 ppm to 10 wt%; and
a remainder including silver (Ag) and other inevitable impurities.

2. The bonding wire of claim 1, further comprising at least one selected from a group consisting of copper (Cu), platinum (Pt), rhodium (Rh), osmium (Os), gold (Au), and palladium (Pd) at 0.03 wt% to 10 wt%.

3. The bonding wire of claim 1 or claim 2, further comprising at least one selected from a group consisting of beryllium (Be), calcium (Ca), magnesium (Mg), barium (Ba), lanthanum (La), cerium (Ce), and yttrium (Y) at 3 ppm to 5 wt%.

4. A light emitting diode (LED) package comprising an LED chip, a lead frame for supplying power to the LED chip, and a bonding wire for connecting the LED chip and the lead frame, wherein the bonding wire is a bonding wire for semiconductor devices according to any one of claims 1 to 3.

5. A method of manufacturing a bonding wire for semiconductor devices, comprising the steps of:
pouring a silver (Ag) alloy, including at least one selected from a group consisting of zinc (Zn), tin (Sn), and nickel (Ni) at 5 ppm to 10 wt% and a remainder including silver (Ag) and other inevitable impurities, into a mold and melting the silver (Ag) alloy;
continuously casting the melted silver (Ag) alloy; and

drawing the continuously casted silver (Ag) alloy.

6. The method of claim 5, wherein the silver (Ag) alloy further comprises at least one selected from a group consisting of copper (Cu), platinum (Pt), rhodium (Rh), osmium (Os), gold (Au), and palladium (Pd) at 0.03 wt% to 10 wt%.

7. The method of claim 5 or 6, wherein the silver (Ag) alloy further comprises at least one selected from a group consisting of beryllium (Be), calcium (Ca), magnesium (Mg), barium (Ba), lanthanum (La), cerium (Ce), and yttrium (Y) at 3 ppm to 5 wt%.

8. The method of claim 7, further comprising the step of performing a softening heat treatment on the drawn silver (Ag) alloy.

WHAT IS CLAIMED IS:

1. A bonding wire for semiconductor devices, comprising:

at least one selected from a group consisting of zinc (Zn) at 5×10^{-6} wt% to 10 wt% and tin (Sn), and nickel (Ni) at 0.01 wt% to 0.05 wt%; and

a remainder including silver (Ag).

2. The bonding wire of claim 1, further comprising at least one selected from a group consisting of copper (Cu), platinum (Pt), rhodium (Rh), osmium (Os), gold (Au), and palladium (Pd) at 0.03 wt% to 10 wt%.

3. The bonding wire of claim 2, further comprising at least one selected from a group consisting of beryllium (Be), calcium (Ca), magnesium (Mg), barium (Ba), lanthanum (La), cerium (Ce), and yttrium (Y) at 3×10^{-6} wt% to 5 wt%.

4. A light emitting diode (LED) package comprising an LED chip, a lead frame for supplying power to the LED chip, and a bonding wire for connecting the LED chip and the lead frame, wherein the bonding wire is a bonding wire for semiconductor devices according to any one of claims 1 to 3.

5. A method of manufacturing a bonding wire for semiconductor devices, comprising the steps of:

pouring a silver (Ag) alloy, including at least one selected from a group

consisting of zinc (Zn) and tin (Sn) at 5×10^{-6} wt% to 10 wt%, and nickel (Ni) at 0.01 wt% to 0.05 wt%, and a remainder including silver (Ag), into a mold, and melting the silver (Ag) alloy;

continuously casting the melted silver (Ag) alloy; and

drawing the continuously casted silver (Ag) alloy.

6. The method of claim 5, wherein the silver (Ag) alloy further comprises at least one selected from a group consisting of copper (Cu), platinum (Pt), rhodium (Rh), osmium (Os), gold (Au), and palladium (Pd) at 0.03 wt% to 10 wt%.

7. The method of claim 5 or 6, wherein the silver (Ag) alloy further comprises at least one selected from a group consisting of beryllium (Be), calcium (Ca), magnesium (Mg), barium (Ba), lanthanum (La), cerium (Ce), and yttrium (Y) at 3×10^{-6} wt% to 5 wt%.

8. The method of claim 7, further comprising the step of performing a softening heat treatment on the drawn silver (Ag) alloy.